

**Complete if Known**

(Use as many sheets as necessary)

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Application Number	10/654189
Filing Date	Sept 3, 2003
First Named Inventor	Ashton et al
Art Unit	2824 2891
Examiner Name	Wilson, Christian D.
Attorney Docket Number	100201669-1

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**Examiner
Signature**

Christina Wilson

Date
Considered

3/23/08

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REFERENCE DESIGNATION	U.S. PATENT DOCUMENTS
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PATENT APPLICATION

Sheet 2 of 5

FORM PTO-1449 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO. 100201669-1	APPLICATION NO. 10/654189	CONFIRMATION NO.
APPLICANT Ashton, et al			
FILING DATE Sept. 3, 2003		GROUP 2829	

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
	2A			
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FOREIGN PATENT DOCUMENTS

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2L				
2M				
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2O				
2P				

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

<div style="text-align: center;"> </div>	2Q	Scofield, et al. Sputtered molybdenum bilayer back contact for copper indium diselenide-based polycrystalline thin-film solar cells; Thin Solid Films (1995) pgs. 26-31
<div style="text-align: center;"> </div>	2R	Gabor, et al. High-efficiency CuIn _x Ga _{1-x} Se ₂ solar cells made from (In _x Ga _{1-x}) ₂ Se ₃ precursor films; American Institute of Physics, (1994) pgs. 198-200
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3/22/05

PATENT APPLICATION

Sheet 3 of 5

FORM PTO-1449 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO.	APPLICATION NO.	CONFIRMATION NO.
	100201669-1	10/654189	
	APPLICANT		
	Ashton, et al		
	FILING DATE	GROUP	
	Sept. 3, 2003	2829	

REFERENCE DESIGNATION

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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

3Q	Nishida, et al. Single-beam overwrite experiment using In-Se based phase-change optical media; American Institute of Physics (1987) pgs. 667-669
3R	Sanchez-Royo, et al. Optical and photovoltaic properties of indium selenide thin films prepared by van der Waals epitaxy; Journal of Applied Physics (2001) pgs. 2818-2823
3S	Otsmane, et al. Epitaxy of layered semiconductor thin films; Applied Surface Science (1993) pgs. 479-481

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REFERENCE DESIGNATION		U.S. PATENT DOCUMENTS			
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4Q	Emery, et al. Reflection high-energy electron diffraction studies of InSe and GaSe layered compounds grown by molecular beam epitaxy; Journal of Applied Physics (1992) pgs. 3256-3259
4R	Tatsuyama, et al. Heteroepitaxy between layered semiconductors GaSe and InSe; Applied Surface Science (1989) pgs. 539-543
4S	Gashimzade, et al. Energy spectrum and effective mass of carriers in the InSe/GaSe superlattice; Z. Physics (1996) pgs. 219-222

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PATENT APPLICATION

Sheet 5 of 5

FORM PTO-1449 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO.	APPLICATION NO.	CONFIRMATION NO.
	100201669-1	10/054189	
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EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
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EXAMINER

Christa Witsa

DATE CONSIDERED

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